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Vishay Siliconix

Automotive N-Channel 30 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY					
V _{DS} (V)	30				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0038				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0050				
I _D (A)	32				
Configuration	Single				

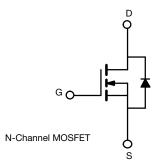
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



ORDERING INFORMATION	
Package	SO-8
Lead (Pb)-free and halogen-free	SQ4182EY (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATING	iS ($T_C = 25 ^{\circ}C$, unless	otherwise noted	1)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	30	\/
Gate-source voltage		V _{GS}	± 20	V
Continuous drain current	T _C = 25 °C ^a	l _D	32	
	T _C = 125 °C		18	
Continuous source current (diode conduction)		Is	6.4	Α
Pulsed drain current b		I _{DM}	100	
Single pulse avalanche current	1 0.1 ml 1	I _{AS}	60	
Single pulse avalanche energy	L = 0.1 mH	E _{AS}	180	mJ
Maximum power dissipation ^b	T _C = 25 °C	D	7.1	10/
	T _C = 125 °C	P_{D}	2.3	W
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount c	R_{thJA}	80	°C/W	
Junction-to-foot (drain)		R_{thJF}	21	C/VV	

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)



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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static	·						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		30	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \mu A$		2.0	2.5	V
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 30 V	-	-	1	μΑ
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 30 V, T _J = 125 °C	-	-	50	
		$V_{GS} = 0 V$	V _{DS} = 30 V, T _J = 175 °C	-	-	250	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	20	-	-	Α
		V _{GS} = 10 V	I _D = 14 A	-	0.0031	0.0038	Ω
Duning and the second of the s		V _{GS} = 10 V	I _D = 14 A, T _J = 125 °C	-	-	0.0060	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 14 A, T _J = 175 °C	-	-	0.0070	
		V _{GS} = 4.5 V	I _D = 10 A	-	0.0040	0.0050	
Forward transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 14 A		-	107	-	S
Dynamic ^b					•		,
Input capacitance	C _{iss}			-	4313	5400	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{GS} = 0 V V _{DS} = 15 V, f = 1 MHz		868	1090	рF
Reverse transfer capacitance	C _{rss}	1		-	305	390	
Total gate charge c	Qg			-	72	110	
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$	-	14	-	nC
Gate-drain charge ^c	Q _{gd}			-	8	-	
Gate resistance	R_g	f = 1 MHz		0.9	1.8	4.9	Ω
Turn-on delay time ^c	t _{d(on)}				16	24	
Rise time ^c	t _r	V_{DD} = 15 V, R_L = 1.5 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω		=	10	15	- ns
Turn-off delay time ^c	t _{d(off)}			-	57	86	
Fall time ^c	t _f			-	8	12	
Source-Drain Diode Ratings and Cha	racteristics b	,			<u> </u>		
Pulsed current ^a	I _{SM}				-	100	Α
Forward voltage	V _{SD}	I _F =	I _F = 10 A, V _{GS} = 0 V		0.75	1.2	V
	•	•			•		

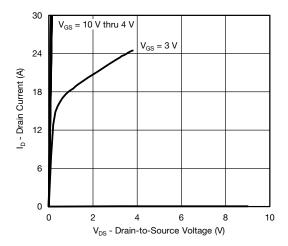
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

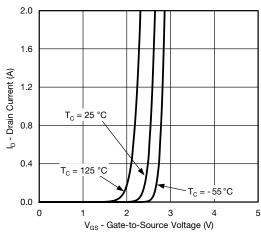
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



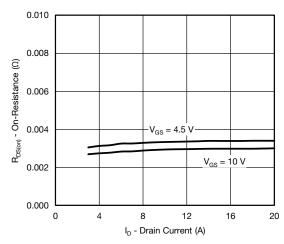
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



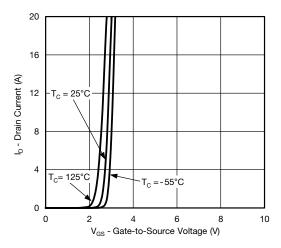
Output Characteristics



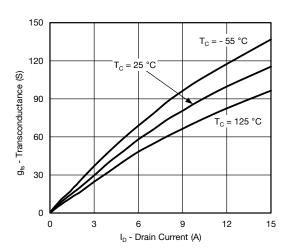
Transfer Characteristics



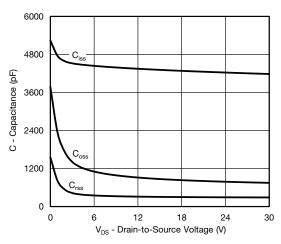
On-Resistance vs. Drain Current



Transfer Characteristics



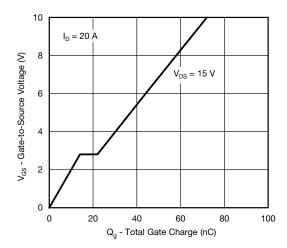
Transconductance



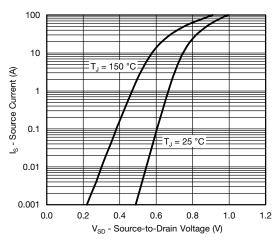
Capacitance



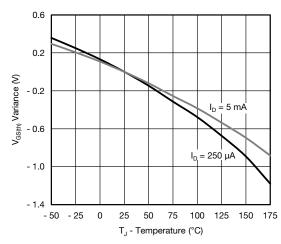
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



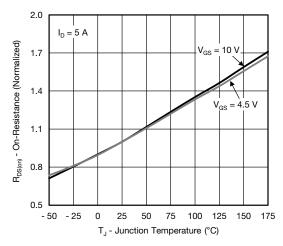
Gate Charge



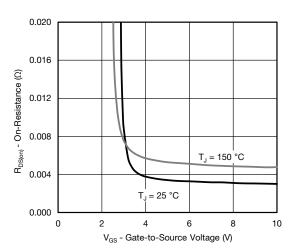
Source Drain Diode Forward Voltage



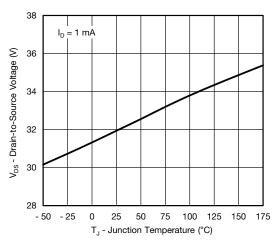
Threshold Voltage



On-Resistance vs. Junction Temperature



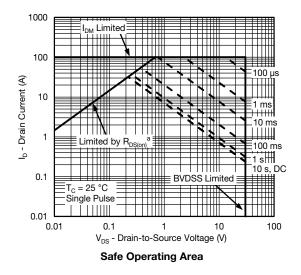
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

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THERMAL RATINGS ($T_A = 25 \, ^{\circ}\text{C}$, unless otherwise noted)

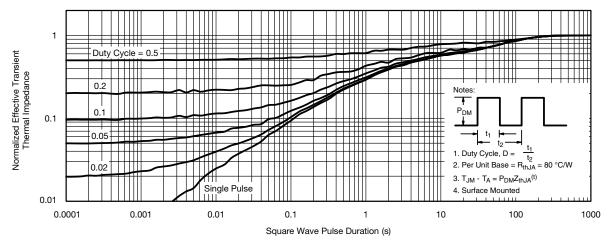


Note

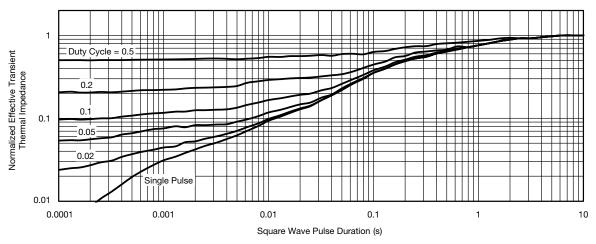
a. $V_{GS} > minimum \ V_{GS}$ at which $R_{DS(on)}$ is specified



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

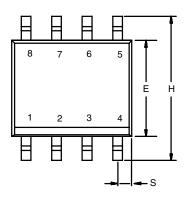
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

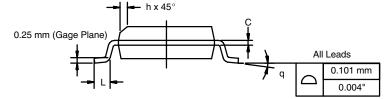
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67917.

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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIMETERS		INC	HES	
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
Е	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050) BSC	
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I. 11-Sep-06					

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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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